

#### Dual P-Channel Enhancement Mode MOSFET

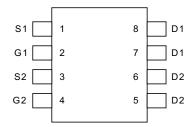
### **Features**

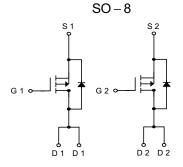
# Pin Description

- -30V/-4.9A,  $R_{DS(ON)} = 53m\Omega(typ.)$  @  $V_{GS} = -10V$  $R_{DS(ON)} = 80m\Omega(typ.)$  @  $V_{GS} = -4.5V$
- Super High Density Cell Design
- Reliable and Rugged
- SO-8 Package

# Applications

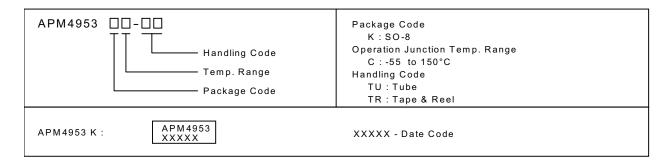
Power Management in Notebook Computer,
Portable Equipment and Battery Powered
Systems





P-Channel MOSFET

### Ordering and Marking Information



### Absolute Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	±25	V
I <sub>D</sub> *	Maximum Drain Current – Continuous T <sub>A</sub> = 25°C	-4.9	Δ
I <sub>DM</sub>	Maximum Drain Current – Pulsed	-30	

<sup>\*</sup> Surface Mounted on FR4 Board, t ≤ 10 sec.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.



# Absolute Maximum Ratings (Cont.) (T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit	
$P_D$	Maximum Power Dissipation $T_A = 25^{\circ}C$		2.5	W
		T <sub>A</sub> = 100°C	1.0	VV
TJ	Maximum Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature Range		-55 to 150	, C
$R_{\scriptscriptstyle{\theta}JA}^{}^{\star}}$	Thermal Resistance - Junction to Ambien	t	50	°C/W

### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Cumbal	Parameter	Test Condition		APM4953		
Symbol	Symbol Farameter Test Condition		Min.	Typ <sup>a</sup> .	Max.	Unit
Static						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>DS</sub> =-250μA	-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V			-1	μΑ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=-250\mu A$	-1	-1.5	-2	V
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}$ =±25V , $V_{DS}$ =0V			±100	nA
D	Drain-Source On-state	V <sub>GS</sub> =-10V , I <sub>DS</sub> =-4.9A		53	60	
R <sub>DS(ON)</sub>	Resistance <sup>b</sup>	V <sub>GS</sub> =-4.5V , I <sub>DS</sub> =-3.6A		80	95	mΩ
V <sub>SD</sub>	Diode Forward Voltage <sup>b</sup>	I <sub>SD</sub> =-1.7A , V <sub>GS</sub> =0V		-0.7	-1.3	V
Dynamic <sup>a</sup>			•			
$Q_g$	Total Gate Charge	V <sub>DS</sub> =-15V , I <sub>GS</sub> =-10V		22.3	29	
$Q_gs$	Gate-Source Charge	I <sub>D</sub> =-4.6A		4.65		nC
$Q_{gd}$	Gate-Drain Charge			2		
t <sub>d(ON)</sub>	Turn-on Delay Time	V <sub>DD</sub> =-15V , I <sub>D</sub> =-2A ,		10	18	
T <sub>r</sub>	Turn-on Rise Time	$V_{GEN}$ =-10V , $R_{G}$ =6 $\Omega$		15	20	
$t_{d(OFF)}$	Turn-off Delay Time			22	38	ns
T <sub>f</sub>	Turn-off Fall Time	R <sub>L</sub> =7.5Ω		15	25	
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V		1260		_
Coss	Output Capacitance	V <sub>DS</sub> =-25V		340		рF
C <sub>rss</sub>	Reverse Transfer Capacitance	Frequency=1.0MHz		220		

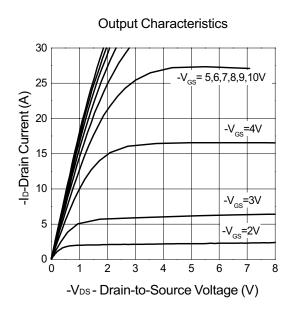
#### Notes

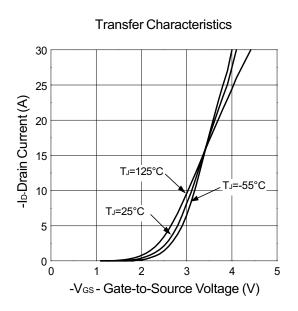
 $^{\rm a}$  : Pulse test ; pulse width  ${\leq}300\mu s,$  duty cycle  ${\leq}\,2\%$ 

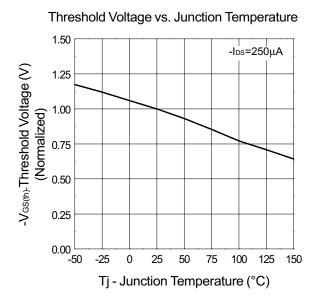
b: Guaranteed by design, not subject to production testing

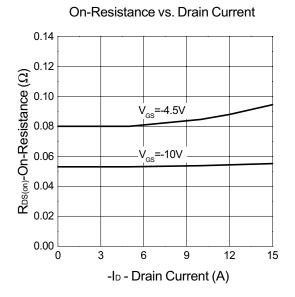


# **Typical Characteristics**



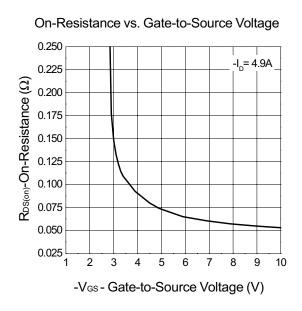


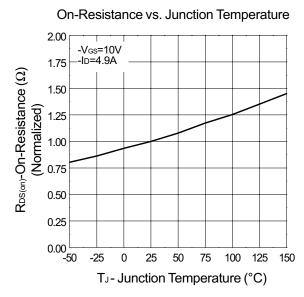


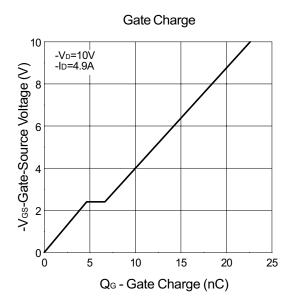


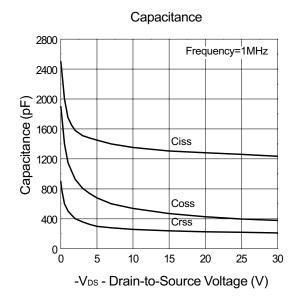


### Typical Characteristics (Cont.)



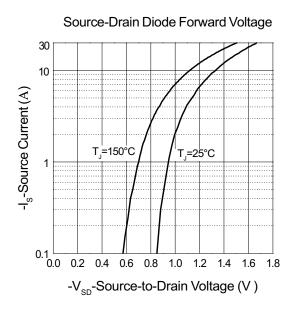


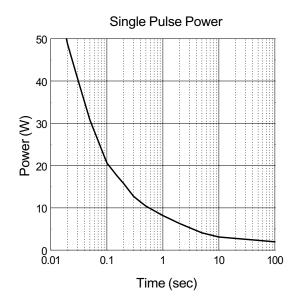




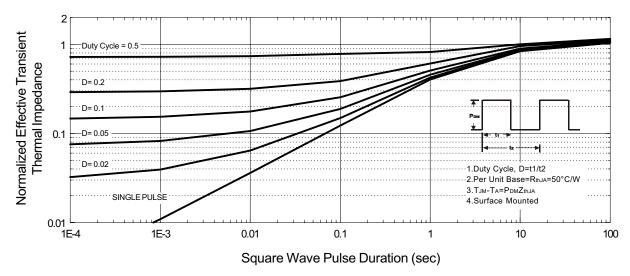


### Typical Characteristics (Cont.)





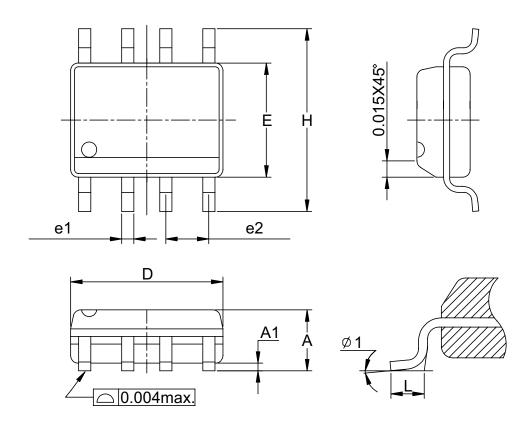
#### Normalized Thermal Transient Impedence, Junction to Ambient





# Packaging Information

SOP-8 pin (Reference JEDEC Registration MS-012)



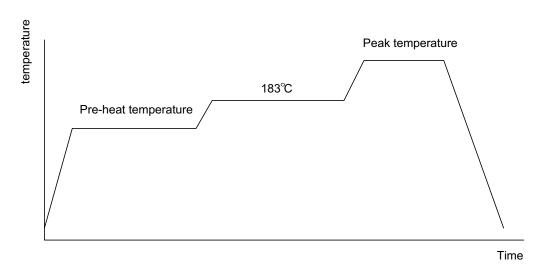
Dim	Millim	neters	Incl	nes
	Min.	Max.	Min.	Max.
Α	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	5.00	0.189	0.197
E	3.80	4.00	0.150	0.157
Н	5.80	6.20	0.228	0.244
L	0.40	1.27	0.016	0.050
e1	0.33	0.51	0.013	0.020
e2	1.27BSC		0.50BSC	
φ 1	8°		8	0



# **Physical Specifications**

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb)
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

### Reflow Condition (IR/Convection or VPR Reflow)



### **Classification Reflow Profiles**

	Convection or IR/ Convection	VPR
Average ramp-up rate(183°C to Peak)	3°C/second max.	10 °C /second max.
Preheat temperature 125 ± 25°C)	120 seconds max	
Temperature maintained above 183°C	60 – 150 seconds	
Time within 5°C of actual peak temperature	10 –20 seconds	60 seconds
Peak temperature range	220 +5/-0°C or 235 +5/-0°C	215-219°C or 235 +5/-0°C
Ramp-down rate	6 °C /second max.	10 °C /second max.
Time 25°C to peak temperature	6 minutes max.	

### Package Reflow Conditions

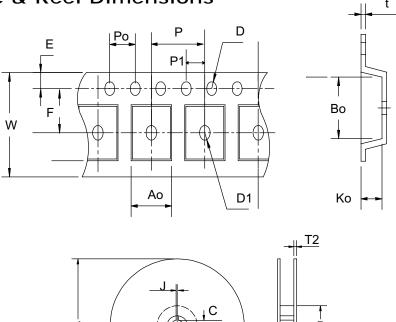
. •	- <del>-</del>	pkg. thickness < 2.5mm and pkg. volume < 350mm³
Convection 220 +5/-0 °C		Convection 235 +5/-0 °C
VPR 215-219 °C		VPR 235 +5/-0 °C
IR/Convection 220 +5/-0 °C		IR/Convection 235 +5/-0 °C



# Reliability test program

Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C,5 SEC
HOLT	MIL-STD 883D-1005.7	1000 Hrs Bias @ 125°C
PCT	JESD-22-B, A102	168 Hrs, 100% RH, 121°C
TST	MIL-STD 883D-1011.9	-65°C ~ 150°C, 200 Cycles

# Carrier Tape & Reel Dimensions



Application	Α	В	С	J	T1	T2	W	Р	E
	330 ± 1	62 +1.5	12.75+ 0.15	2 ± 0.5	12.4 ± 0.2	2 ± 0.2	12± 0. 3	8± 0.1	1.75±0.1
SOP-8	F	D	D1	Po	P1	Ao	Во	Ko	t
	5.5± 1	1.55 +0.1	1.55+ 0.25	4.0 ± 0.1	2.0 ± 0.1	6.4 ± 0.1	5.2± 0. 1	2.1± 0.1	0.3±0.013

T1



### **Cover Tape Dimensions**

Application	Carrier Width	Cover Tape Width	Devices Per Reel
SOP-8	12	9.3	2500

### **Customer Service**

#### **Anpec Electronics Corp.**

Head Office:

5F, No. 2 Li-Hsin Road, SBIP,

Hsin-Chu, Taiwan, R.O.C.

Tel: 886-3-5642000 Fax: 886-3-5642050

Taipei Branch:

7F, No. 137, Lane 235, Pac Chiao Rd.,

Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.

Tel: 886-2-89191368 Fax: 886-2-89191369